PATENT ABSTRACTS OF JAPAN

(11)Publication number:

08-134606

(43)Date of publication of application: 28.05.1996

(51)Int.ÇI:

C22C 38/00 H01F 1/16

(21)Application number: 06-276790

(71)Applicant:

NIPPON STEEL CORP

(22)Date of filing:

10.11.1994

(72)Inventor:

KAWAMATA RYUTARO

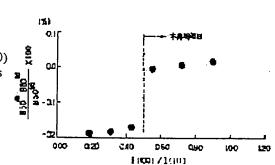
KUBOTA TAKESHI YAMADA KENJI

(54) NONORIENTED SILICON STEEL SHEET HAVING HIGH MAGNETIC FLUX DENSITY AFTER STRESS **RELIEF ANNEALING**

(57) Abstract:

PURPOSE: To produce a nonoriented silicon steel sheet having high magnetic flux density after stress relief annealing by forming a texture, satisfying the prescribed conditions, in a steel sheet before stress relief annealing, in a nonoriented silicon steel sheet containing specific amounts of Si and C.

CONSTITUTION: A nonoriented silicon steel sheet, containing, by weight, &le,7.00% Si and &le,0.010% C in steel and used for iron core for use in electrical equipment, such as rotary machine iron core and transformer iron core, is provided, before stress relief annealing, with a texture in which I(100) and I(111) as the values of the ratios of the X-ray reflected surface intensities of (100) and (111) orientations in the pseudoplane parallel to a sheet surface in the part between the surface layer and a position at a depth one-fifth the sheet thickness from the surface layer to a random texture, satisfy relational inequality 0.50≤I(100)/I(111). By this method, the nonoriented silicon steel sheet having high magnetic flux density after stress relief annealing can be obtained.



LEGAL STATUS

[Date of request for examination]

31.08.2000

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2000 Japan Patent Office